## Effect of Spin-Orbit Coupling and Other Relativistic Corrections on Donor States in Ge and Si

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(Received 14 June 1963)

Four corrections to the effective-mass approximation are considered with first-order perturbation theory; namely, the deviation of the total perturbing potential U from the potential  $U_0 = -e^2/\kappa r$  ( $\kappa =$  static dielectric constant) and the three relativistic corrections: (a) spin-orbit coupling, (b) s-shift correction, and (c) massvelocity correction. The number of independent matrix elements is determined for each perturbation by means of the selection-rule theorem. There is no effect of spin-orbit coupling on the effective-mass ground state; the corresponding effect on the exact eigenstates of the nonrelativistic Hamiltonian appears to be small for donors in Si, and does not cause a splitting of the sextet state (with spin) in Ge or Si. Both of the other two relativistic corrections give rise to a shift and a splitting of the degenerate effective-mass ground state, as does the perturbation  $U - U_0$ . The magnitude of the relativistic corrections and their relative contribution to the observed splitting of the effective-mass ground state are discussed briefly.

#### I. INTRODUCTION

 $\mathbf{I}^{N}$  this paper, some of the corrections to the effective-mass theory<sup>1</sup> of shallow donor states in Ge and Si will be studied. The simple effective-mass equation for the motion of a donor electron in the perturbed periodicpotential field of a germanium or silicon crystal accounts for a qualitatively correct picture of the stationary eigenstates of donor electrons. The energy spectra of different donor impurities (P, As, Sb) in silicon have been determined experimentally from infrared-absorption measurements, and quantitative agreement has been found between theory and experiment, with the exception of the ground state.<sup>2</sup> There are, however, some discrepancies between theory and experiment with respect to the ground-state energy and the amplitude of its effective-mass wave function at a donor site. Kohn and Luttinger<sup>3</sup> have shown that the effectivemass wave function can be corrected for by a simple semiempirical procedure, using the observed energy of the lowest donor state. It has been recognized by the same authors that the discrepancies are caused by the breakdown of the effective-mass formalism in the immediate neighborhood of the impurity ion where the perturbing potential is large and varies strongly with distance from the impurity nucleus. Therefore, several corrections to the effective-mass theory are necessary. These corrections are discussed in Sec. II where the problem is also formulated so it can be treated by first-order perturbation theory. In Sec. III, a grouptheoretical analysis is presented to determine the number of independent constants for the matrixes of the perturbation components with the help of the selection-rule theorem. Section IV is concerned with a brief qualitative discussion of the relative magnitudes of the different perturbations considered in this paper.

#### **II. CORRECTIONS—FORMULATION OF** THE PROBLEM

If one neglects the effects of lattice vibrations, there are three corrections which affect the effective-mass ground state:

(1) the deviation of the total perturbing potential  $U(\mathbf{r})$  from  $U_0(\mathbf{r}) = -e^2/\kappa \mathbf{r}$  due to the self-consistent potential of the impurity ion in the central cell region being different from that of a Ge or Si atom—the effect of local strain introduced by the impurity, and polarization effects (see Ref. 7 below);

(2) the admixture of Bloch functions from higher bands into the impurity wave function caused by the strong potential U near the impurity ion; and

(3) relativistic corrections: (a) spin-orbit coupling; (b) s-shift correction, and (c) mass-velocity correction.

It is a characteristic property of these corrections that the major contribution of each of them comes from the central cell; that is, the atomic cell containing the impurity ion. Thus, in calculating their effect on the effective-mass ground state, there are two technical difficulties. First, one must know the correct form of the perturbing potential  $U(\mathbf{r})$  within the central cell. This potential is known for small  $r \ll a_0 (=5.29 \times 10^{-9})$ cm) and for large  $r \gg r_s$   $(\frac{4}{3}\pi r_s^3 = \frac{1}{2}\Omega)$ , where  $\Omega$  is the unit cell volume).<sup>3</sup> The symmetry of  $U(\mathbf{r})$  is that of a lattice site and is given by the tetrahedral point group. Second, the Bloch functions admixed into the impurity wave function must be known. However, at present one knows only the approximate Bloch functions of the lowest conduction band. In the case of Ge and Si, these functions are suitable admixtures of 4s and 4patomic orbitals, and of 3s and 3p atomic orbitals, respectively. Thus, we shall neglect the admixtures of Bloch functions from higher bands into an impurity wave function and shall consider only the effects of corrections (1) and (3).

A primary motivation for this consideration is a grouptheoretical analysis of the four perturbations associated

<sup>&</sup>lt;sup>1</sup> J. M. Luttinger and W. Kohn, Phys. Rev. 97, 869 (1955); M. Luttinger and W. Kohn, Phys. Rev. 91, 609 (1953);
W. Kohn, in Solid State Physics, edited by F. Seitz and D. Turnbull (Academic Press Inc., New York, 1957), Vol. 5.
<sup>2</sup>G. S. Picus, E. Burnstein, and B. Henvis, J. Phys. Chem. Solids 1, 75 (1956); see also W. Kohn, Phys. Rev. 98, 1856 (1955).
<sup>3</sup> W. Kohn and J. M. Luttinger, Phys. Rev. 97, 883 (1955).

with corrections (1) and (3). It is of particular interest to know how the eightfold and twelvefold degenerate effective-mass ground states, including spin-degeneracy, of donor electrons in Ge and Si, respectively, split under the influence of these corrections. This question is of interest because a number of experimental investigations have been carried out in an original manner to determine the structure of the energy levels emerging from the degenerate effective-mass ground state (see Fig. 1).<sup>4</sup> The experimental information on the energylevel scheme of those impurity states which emerge from the degenerate effective-mass ground state gives rise to two questions: (1) to what extent do the three relativistic corrections account for the observed energy levels; and (2) how large is the additional splitting to be expected from spin-orbit coupling? This problem is formulated with the two-component Pauli equation<sup>5</sup>

$$\begin{bmatrix} \mathbf{p}^{2} \\ 2m \end{bmatrix} + \mathbf{\upsilon} + \frac{\hbar}{4m^{2}c^{2}} (\mathbf{\nabla}\mathbf{\upsilon} \times \mathbf{p}) \cdot \mathbf{\sigma} + \frac{\hbar}{4im^{2}c^{2}} (\mathbf{\nabla}\mathbf{\upsilon} \cdot \mathbf{p}) \\ - \frac{1}{2mc^{2}} (E_{0} + \mathbf{\upsilon})^{2} \end{bmatrix} \Psi = E\Psi, \quad (1)$$

where  $E_0$  is the lowest energy eigenvalue of the nonrelativistic Hamiltonian  $H_0$  defined below. The second term is the total potential energy of an impurity electron,

$$\mathcal{U}(\mathbf{r}) = V(\mathbf{r}) + U(\mathbf{r}), \qquad (2)$$

where  $V(\mathbf{r})$  is an effective periodic potential. The three last terms of Eq. (1) are peculiar to the relativistic theory and correspond to the corrections (3a), (3b), and (3c). We mention that the *s*-shift correction shifts the *s* terms of a free atom (pure Coulomb potential), but contributes nothing to p, d, and higher terms.<sup>6</sup> The stationary states of Eq. (1), its eigenvalues, and the associated two-component wave functions, cannot be



FIG. 1. Energy-level scheme, neglecting the spin-degeneracy, for singlet (s) and doublet (d) states of donors in silicon and for singlet and triplet (t) states for donors in germanium after Wilson and Feher, and Fritzsche. (See Ref. 4.) The splitting between doublet and triplet states for donors in Si is assumed to be zero (em = energy of effective-mass ground state).

calculated without an approximation. In the next section the problem is treated by perturbation theory.

## **III. PERTURBATION THEORY**

The nonrelativistic problem with the Hamiltonian

$$H_0 = (\mathbf{p}^2/2m) + V(\mathbf{r}) + U_0(\mathbf{r})$$
 (3)

has been treated by Kohn and Luttinger.<sup>1</sup> The impurity potential  $U_0 = -e^2/\kappa r$ , where  $\kappa$  is the static dielectric constant.<sup>7</sup> An eigenfunction of  $H_0$  can be developed, in terms of Bloch functions, for electrons moving in the periodic potential  $V(\mathbf{r})$ :

$$\boldsymbol{\psi} = \sum_{n,\mathbf{k}} A_n(\mathbf{k}) \boldsymbol{\psi}_n(\mathbf{k},\mathbf{r}) , \qquad (4)$$

where n labels the conduction bands. In the effectivemass approximation, a donor wave function is written as an appropriate linear combination of wave functions

$$\psi_i = \sum_{\mathbf{k}} A_0(\mathbf{k} - \mathbf{k}_i) \psi_0(\mathbf{k} - \mathbf{k}_i, \mathbf{r}), \qquad (5)$$

where  $i=1, 2, \dots, m$  correspond to the minima of the lowest conduction band, n=0. Assuming that  $A_0$  has appreciable magnitude only in the vicinity of  $\mathbf{k}_i$ , one can rewrite Eq. (5) to a lowest approximation, in the form

$$\psi_i = F_i(\mathbf{r})\psi_0(\mathbf{k}_i, \mathbf{r}) , \qquad (6)$$

 $A_0(\mathbf{k}-\mathbf{k}_i)\exp(i\mathbf{k}_i\cdot\mathbf{r})$ 

where 
$$F_i(\mathbf{r}) = \sum_{\mathbf{k}}$$

is the envelope function, i.e, an eigenfunction of the effective mass equation. The wave function  $\psi_i$  is normalized as usual (see Ref. 3).

<sup>&</sup>lt;sup>4</sup> The results summarized in Fig. 1 have been obtained by experimental investigations of a different nature: (1) The change of the electron spin resonance spectrum of donor electrons in Si has been investigated by D. K. Wilson and F. Feher, Phys. Rev. **124**, 1068 (1961). (2) The low-temperature electrical resistivity of antimony-doped Ge under uniaxial strain and compression has been measured by F. Fritzsche, Phys. Rev. **125**, 1560 (1961); Twose shows in an appendix to Fritzsche's paper, that, even in the effective-mass approximation, there is a small splitting of the degenerate ground state; this splitting is neglected here. (3) The strain-induced shifts of the absorption lines of the Lyman series for donor electrons in Ge have been observed by G. Weinreich, W. S. Boyle, H. A. White, and K. F. Rodgers, Phys. Rev. Letters **3**, 244 (1959).

<sup>&</sup>lt;sup>6</sup> This equation is derived from the four-component Dirac equation under the assumption that at all points in the configuration space, two components are small compared to the other two. This assumption is justified (in zero magnetic field) if the first two terms of Eq. (1) are small compared with the restenergy of an electron.

The present case the potential  $V(\mathbf{r})$  are binar compared with the rest energy of an electron. <sup>6</sup> E. U. Condon and A. H. Shorley, *Theory of Atomic Spectra* (Cambridge University Press, Cambridge, England, 1958), p. 125. In the present case the potential  $V(\mathbf{r})$ —and in particular  $U(\mathbf{r})$ —is not a pure Coulomb potential and, therefore, the so-called *s*-shift correction does contribute very slightly to Bloch states and to impurity states which are not pure *s* states.

<sup>&</sup>lt;sup>7</sup> K. Müller [dissertation, Braunschweig, 1960 (unpublished)] has investigated in some detail the polarization field near a point charge located at a lattice site of a cubic semiconductor. He employs a technique similar to Ewald's method of long waves to obtain the corrections to the continuum polarization. A deformation of the potential  $U_0$  occurs for distances r < 3a(a = lattice constant) because of a dispersion of the polarizability for short wavelengths and because of a local dielectric anisotropy near the point change.

| Class  | 1E                    | $1ar{E}$              | $6C_{4}^{2}$   | 8 <i>C</i> ₃                                | $8\bar{C}_3$                                | 6 <i>S</i> 4   | $6ar{S}_4$   | $12\sigma_d$              |
|--|-----------------------|-----------------------|--|---|---|--|--|---------------------------|
| ${}^{1}\Gamma_{1}$<br>${}^{1}\Gamma_{2}$<br>${}^{2}\Gamma_{3}$<br>${}^{3}\Gamma_{4}$<br>${}^{3}\Gamma_{5}$ | 1<br>1<br>2<br>3<br>3 | 1<br>1<br>2<br>3<br>3 | $     \begin{array}{r}       1 \\       1 \\       2 \\       -1 \\       -1 \\       -1     \end{array} $ | $\begin{array}{c}1\\1\\-1\\0\\0\end{array}$ | $\begin{array}{c}1\\1\\-1\\0\\0\end{array}$ | $     \begin{array}{c}       1 \\       -1 \\       0 \\       -1 \\       1     \end{array} $ | $     \begin{array}{c}       1 \\       -1 \\       0 \\       -1 \\       1     \end{array} $ | $-1 \\ -1 \\ 0 \\ 1 \\ 1$ |
| $^{2}\Gamma_{6}$ $^{2}\Gamma_{7}$ $^{4}\Gamma_{8}$   | $2 \\ 2 \\ 4$         | $-2 \\ -2 \\ -4$      | 0<br>0<br>0  | 1<br>1<br>-1                                | $-1 \\ -1 \\ 1$                             | $-{2 \atop 0}^{2}$   | $-2 \\ -2 \\ 0$  | 0<br>0<br>0               |
| Ge, "1s" state<br>with spin<br>Si, "1s" state<br>with spin   | 8<br>12               | -8<br>-12             | 0<br>0   | 1<br>0                                      | -1<br>0                                     | 0<br>0   | 0<br>0   | 0<br>0                    |

TABLE I. Character table for the tetrahedal double group.<sup>a</sup>

<sup>a</sup> For the symmetry operations of the tetrahedral point group and the associated double group, see G. F. Koster, in *Solid State Physics*, edited by F. Seitz and D. Turnbull (Academic Press Inc., New York, 1957), Vol. 5. The direct products of the double group representations are given by D. Schechter Technical Report No. 4 Carnegie Institute of Technology, March, 1958 (unpublished). The decompositions of symmetric direct products can be determined by a method found in F. D. Murnaghan, *The Theory of Group Representations* (The Johns Hopkins Press, Baltimore, 1938), p. 72.

As the perturbation to the Hamiltonian  $H_0 \cdot 1$  (1 is the unit matrix), we take

$$H' = (U - U_0) \cdot \mathbf{1} + \frac{\hbar}{4m^2c^2} (\nabla \mathcal{V} \times \mathbf{p}) \cdot \sigma$$
$$+ \frac{\hbar}{4im^2c^2} (\nabla \mathcal{V} \cdot \mathbf{p}) \cdot \mathbf{1} - \frac{1}{2mc^2} (E_0 + \mathcal{V})^2 \cdot \mathbf{1}. \quad (7)$$

The first term of Eq. (7) is the deviation of the actual impurity potential from the potential  $U_0$  of the effectivemass equation; the other terms represent the *relativistic* corrections which depend on the total potential U. Taking the eigenfunction of  $H_0$  given by the effectivemass approximation and multiplied by an arbitrary spin function we readily find the correct zeroth-order wave function corresponding to H' from symmetry considerations.

Germanium. The lowest effective-mass eigenstate is eightfold degenerate when the spin degeneracy is included. This state belongs to a reducible representation of the tetrahedral double group  $\bar{T}_d$ ; a perturbation can split this state into three states associated with the representations  ${}^{2}\Gamma_{6}$ ,  ${}^{2}\Gamma_{7}$ , and  ${}^{4}\Gamma_{8}$  as seen from Table I. The correct zeroth-order wave function, which forms a basis for an irreducible representation  ${}^{t}\Gamma_{s}$  of  $\overline{T}_{d}$ , is written in the form

$$\Psi_{rs} = \sum_{i} \left( \alpha_i^{rs} \phi_i + \beta_i^{rs} \chi_i \right), \quad (r = 1, 2, \cdots t), \qquad (8)$$

where the two-component wave functions  $\phi_i$  and  $\chi_i$ are related by time reversal symmetry; i.e., Wigner's operation K for spin one-half particles,<sup>8</sup>

<sup>8</sup> The time reversal operation  $K = i\sigma_y K_0$ , where  $K_0$  is the complex conjugation operator.

The wave functions  $\psi_i$  are given by Eq. (6), if not explicitly noted otherwise. The two normalized spin functions  $u_+$  and  $u_-$ , as well as the linear combinations  $u_++u_-$  and  $u_--u_+$ , form a basis for the representation  ${}^{2}\Gamma_{6}$ .<sup>9</sup> The formal advantage for choosing the 2m spin functions  $\phi_i$  and  $\chi_i$  as components of the zeroth-order wave functions  $\Psi_{rs}$ , instead of spin-up and spin-down functions, is suggested by the time reversal symmetry between  $\phi_i$  and  $\chi_i$ . Hence, one immediately finds the time-reversed wave function of  $\Psi_{rs}$ ; it is

$$K\Psi_{rs} = \sum_{i} \left[ (\alpha_i^{rs})^* \chi_i + (\beta_i^{rs})^* \phi_i \right], \tag{10}$$

which, according to Kramer's theorem, also belongs to the basis given by Eq. (8). There is no additional degeneracy of an eigenstate associated with  ${}^{2}\Gamma_{6}$ ,  ${}^{2}\Gamma_{7}$ , or  ${}^{4}\Gamma_{8}$  because of time reversal symmetry; the above representations fall under Wigner's case (c),<sup>10</sup> as does the small representation of the Bloch state for the conduction band minimum. The coefficients  $\alpha_i^{rs}$  and  $\beta_i^{rs}$  are calculated in Appendix A; the results are: for  $({}^{2}\Gamma_{6})$ ,

$$\begin{array}{ll}
\alpha_i^{16} = \frac{1}{2}(1,1,1,1), & \alpha_i^{26} = \beta_i^{16}, \\
\beta_i^{16} = (0,0,0,0), & \beta_i^{26} = \alpha_i^{16};
\end{array}$$
(11a)

for  $({}^{2}\Gamma_{7})$ ,

$$\begin{aligned} \alpha_i^{17} &= (1/2\sqrt{3})(1, 1, -1, -1), \\ \beta_i^{17} &= (1/2\sqrt{3})(1-i, i-1, 1-i, i-1), \\ \alpha_i^{27} &= (\beta_i^{17})^*, \\ \beta_i^{27} &= \alpha_i^{17}; \end{aligned}$$
(11b)

and for  $({}^{4}\Gamma_{8})$ ,

$$\begin{aligned} &\alpha_{i}^{18} = (1/2\sqrt{2})(1+i, -1-i, 1-i, i-1), \\ &\beta_{i}^{18} = (0,0,0,0), \\ &\alpha_{i}^{28} = \left[ 1/2(6)^{1/2} \right] (-2, -2, +2, +2), \\ &\beta_{i}^{28} = \left[ 1/2(6)^{1/2} \right] (1+i, -1-i, 1-i, i-1), \\ &\alpha_{i}^{38} = (\beta_{i}^{28})^{*}, \\ &\beta_{i}^{38} = \alpha_{i}^{28}, \\ &\alpha_{i}^{48} = \beta_{i}^{18}, \\ &\beta_{i}^{48} = (\alpha_{i}^{18})^{*}. \end{aligned}$$
(11c)

Silicon. The twelvefold-degenerate effective-mass ground state, including the electron spin, can split under a perturbation into four different states; the appropriate decomposition, as found from Table I, is  ${}^{2}\Gamma_{6} + {}^{2}\Gamma_{7}$  $+2 \,{}^{4}\Gamma_{8}$ . The correct zeroth-order wave functions given by Eq. (8) can be determined with the help of the table of coefficients given in Ref. 1 [Kohn, Eq. (5.46)] by proceeding as in Appendix A for the case of Ge.

<sup>&</sup>lt;sup>9</sup> The complex conjugate spin functions  $u_+^*$  and  $u_-^*$ , as well as the two functions  $u_+^* + u_-^*$  and  $u_-^* - u_+^*$ , transform according to  ${}^{2}\Gamma_{6}^*$  under the symmetry operations of  $T_d$ . <sup>10</sup> E. Wigner, Nachr. Acad. Wiss. Goettingen, Math.-Physik.

Kl. 1932, 546,

The  $\Psi_{rs}$  are the correct zero-order wave functions for the perturbation H'. Thus, the influence of the perturbation on the effective-mass energy levels of the unperturbed Hamiltonian is obtained by evaluating the expectation value of H' in the wave functions  $\Psi_{rs}$ . If one rewrites Eq. (7) in the form

$$H' = \sum_{\kappa} H_{\kappa}, \qquad (12)$$

where  $H_1$  = potential correction,  $H_2$  = spin-orbit coupling correction,  $H_3 = s$ -shift correction,  $H_4 =$  mass-velocity correction, the matrix elements of the four perturbations are given by

$$\int_{a.s.} \Psi_{rs}^* H_k \Psi_{r's'} d\tau , \qquad (13)$$

where a.s. indicates integrations over all space. In order to find the number of independent constants for each perturbation, assuming that the  $\Psi_{rs}$  are given in terms of the effective-mass wave functions  $\psi_i$ , Eq. (6), we proceed in the following way. The matrices in the  $\Psi_{rs}$ representation can be written as a linear combination of matrices in the  $\phi_i$ ,  $\chi_i$  representation; the latter are given by

$$\int_{\mathbf{a.s.}} \phi_i^* H_{\kappa} \phi_j d\tau \quad \text{and} \quad \int_{\mathbf{a.s.}} \phi_i^* H_{\kappa} \chi_j d\tau \,. \tag{14}$$

Taking the case of germanium as an example, we know that the wave functions  $\phi_i$ ,  $\chi_i$  transform according to the representation  $({}^{2}\Gamma_{6}+{}^{2}\Gamma_{7}+{}^{4}\Gamma_{8})$ . The four perturbations  $H_{\kappa}$  are scalar quantities and transform according to  ${}^{1}\Gamma_{1}$ . Thus, in the  $\phi_{i}$ ,  $\chi_{i}$  representation, the selection rule theorem<sup>11</sup> gives at most three independent constants for each perturbation  $H_{\kappa}$ . For the spin-independent perturbations ( $\kappa = 1, 3, 4$ ) two of the three constants must be equal to one another; that is, the energy eigenvalues associated with the representations  ${}^{2}\Gamma_{6}$  and  ${}^{4}\Gamma_{8}$  are not separated by these perturbations since the matrices between  $\phi_i$  and  $\chi_i$  vanish (the spin functions are orthogonal to one another). The spin-independent perturbation ( $\kappa = 2$ ), however, could lift the degeneracy. To find out whether this is actually the case, the spin functions are eliminated from the matrices (14). Then we are left with the expressions

and

$$M_{ij,2} = \int_{\mathbf{a.s.}} \psi_i^* h_x \psi_j d\tau , \quad \mathfrak{M}_{ij,2} = \int_{\mathbf{a.s.}} \psi_i^* h_x \psi_j^* d\tau , \quad (16)$$

 $M_{ij,\kappa} = \int_{a.s.} \psi_i^* H_{\kappa} \psi_j d\tau , \quad (\kappa = 1, 3, 4) ,$ 

(15)

where  $h_x$  is the x component of a pseudo-vector operator

TABLE II. Number of independent constants obtained with the effective-mass approximation  $[\psi_i$  is given by Eq. (6)] for the matrices given by Eqs. (15) and (16).

| Pertur-<br>bation<br>Semi-<br>conductor | Potential correction | Spin-orbit<br>coupling | s-shift<br>correction | Mass-<br>velocity<br>correction |
|---|----------------------|------------------------|-----------------------|---------------------------------|
| Germanium                               | 2                    | 0 (1)                  | 2                     | 2                               |
| Silicon                                 | 3                    | .0 (3)                 | 3                     | 3                               |

**h** defined by the equation<sup>12</sup>

$$H_2 = \mathbf{h} \cdot \boldsymbol{\sigma}. \tag{17}$$

The number of independent constants contained in Eqs. (15) and (16) is determined with the selection rule theorem. The results are found in Table II; they apply also—as can be shown with a lengthy calculation —if the effective-mass wave functions are given by  $\psi_i = \sum_{\mathbf{k}} A_0(\mathbf{k}) \exp(i\mathbf{k}\cdot\mathbf{r}) [u_{\mathbf{k}_i} + (\mathbf{k}-\mathbf{k}_i)\cdot\nabla_{\mathbf{k}-\mathbf{k}_i}u_{\mathbf{k}}]$ , where  $|\mathbf{k}-\mathbf{k}_i| \ll |\mathbf{k}_i|$ ; the derivatives of  $u_k$  are taken at  $\mathbf{k}=\mathbf{k}_i$ . If one goes beyond this effective-mass approximation by assuming that the impurity wave functions contain admixtures of Bloch functions from higher conduction bands, the spin-orbit coupling matrices (16) give one and three independent constants for Ge and Si, respectively, as indicated in Table II.<sup>13</sup> It is emphasized that, in any case, the spin-orbit matrices  $\mathfrak{M}_{ij,2}$  resulting from those matrices (14) which connect time reversal wave functions, such as  $\phi_i$  and  $\chi_j$ , vanish.<sup>14</sup>

In order to discuss the influence of the perturbations  $H_{\kappa}$  on the unperturbed energy levels, let us write down the solutions of that secular problem obtained by taking the scalar product of the two-component wave equation

$$(H_0 \cdot \mathbf{1} + H')\Psi_{rs} = E_s \Psi_{rs} \tag{18}$$

with  $\chi_i$  and  $\phi_i$ . The eigenvalues of the secular matrix are found with the help of the eigenvectors  $\alpha_i^{rs}$ ,  $\beta_i^{rs}$  $(i=1, 2, \cdots m)$ . For germanium we find

$$E_{6} = E_{0} + \sum_{\kappa} (M_{11,\kappa} + M_{21,\kappa} + M_{31,\kappa} + M_{41,\kappa}),$$
  

$$E_{7} = E_{0} + \sum_{\kappa} (M_{11,\kappa} + M_{21,\kappa} - M_{31,\kappa} - M_{41,\kappa}), \quad (19)$$
  

$$E_{8} = E_{7}.$$

<sup>12</sup> Thus  $h_x \psi_i = -(\hbar^2/4m^2c^2) (\nabla \Im \times i \nabla \psi_i)_x$ , etc.

<sup>-1</sup> Into  $n_{\mathcal{S}}\psi_i - (w_i)^{\mathcal{HHC}}(V \otimes \mathcal{N} \otimes \mathcal{V} \psi_i)_x$ , etc. <sup>13</sup> For Ge the basis  $\psi_i$  transforms according to the representation  $\Gamma_1 + \Gamma_4$  of the single group  $T_d$ . The symmetric direct product  $[\Gamma + \Gamma_4]_{sym}^2$  contains the trivial representation  $\Gamma_1$ , according to which  $H_1$ ,  $H_3$ , and  $H_4$  transform, twice. The three components of the pseudovector operator  $\mathbf{h}(h_x,h_y,h_z)$  transform according to  $\mathbf{r}_{\epsilon}$ . Since  $\mathbf{h}$  is a vector operator, but not a vector, we must take  $\Gamma_5$ . Since **h** is a vector operator, but not a vector, we must take the direct product  $\Gamma_5 \times (\Gamma_1 + \Gamma_4)$  and see how often it contains  $\Gamma_1$  and  $\Gamma_4$  in order to determine the number of independent constants for the matrices  $M_{ij,2}$  and  $M_{ij,2}$ . (If, however, **h** were **a** vector, and not a vector operator, we should take the symmetric direct product  $[\Gamma_1 + \Gamma_4]_{sym^2}$  and see how often it contains  $\Gamma_5$ .

<sup>14</sup> Because **h** is imaginary and Hermitian, one has  $\mathfrak{M}_{ij,2}$  $=-\mathfrak{M}_{ji,2}$ . On the other hand, the symmetry requires  $\mathfrak{M}_{ij,2}$  $=\mathfrak{M}_{ji,2}$ ; that is, the solution of the secular problem given below shows that the matrices  $\mathfrak{M}_{ij,2}$  must be real.

<sup>&</sup>lt;sup>11</sup> V. Heine, Group Theory in Quantum Mechanics (Pergamon Press, Ltd., London, 1960).

## IV. DISCUSSION OF THE CORRECTIONS

## A. Potential Correction

The total perturbing potential U can be written in terms of those harmonic functions which are invariant under the symmetry operations of the tetrahedral point group. The first few terms of an expansion of Uare given by

$$U(\mathbf{r}) = f(r) + g(r) \frac{xyz}{r^3} + h(r) \frac{x^4 + y^4 + z^4 - 3r^4/5}{r^4} + \cdots, \quad (20)$$

where<sup>3</sup>

$$\lim_{r \to 0} f(r) = -\frac{e^2(Z_d - Z_0)}{r}, \quad \lim_{r \to \infty} f(r) = U_0(r),$$

 $Z_d$  and  $Z_0$  being the atomic numbers of a donor atom and of a Ge or Si atom, respectively. The harmonic functions of the tetrahedral group are linear combinations of surface spherical harmonics  $Y_l^m$ , with the same subindex *l*. Since spherical harmonics are solutions of the Laplace equation, one finds

$$\lim_{r \to 0} g(r) = Ar^3, \quad \lim_{r \to \infty} g(r) = Br^{-3}, \quad (21)$$

where A and B are constants.

The potential correction  $U - U_0$  causes a shift and a splitting of the degenerate ground state. The shift increases the binding energy and is proportional to the diagonal elements

$$M_{ii,1} = \int_{a.s.} |\psi_i|^2 (U - U_0) d\tau$$
  

$$\simeq \frac{1}{2} |F(0)|^2 \Omega \int_{c.c.} |\psi_0(\mathbf{k}_i, \mathbf{r})|^2 f(r) \frac{2d\tau}{\Omega}, \quad (22)$$

where  $F(0) = F(\mathbf{r} = 0)$  (the index *i* is omitted) and c.c.=central cell. The integral on the right side of Eq. (22) is the average value of the potential energy of a conduction electron; it is of the order of 10 eV. The factor before the integral is given by

$$\frac{1}{2} |F(0)|^2 \Omega = \frac{4}{3} (r_s/a_0^*)^3 = 0.78 \times 10^{-4} \text{ for } \text{Ge}(a_0^* = 45 \text{ Å}),$$
  
= 0.77×10<sup>-3</sup> for Si(a\_0^\* = 20 Å).

Thus, the shift of the effective-mass ground state amounts to  $10^{-3}$  eV and  $10^{-2}$  eV for donors in Ge and Si, respectively. The shifts are larger by one order of magnitude if one takes the amplitudes of the corrected envelope functions (see Ref. 1, Kohn). The splitting of the degenerate effective-mass ground state depends on the off-diagonal elements  $M_{ij,1}$  which contain the anisotropic contribution  $U(\mathbf{r}) - f(r)$  to the perturbing potential. We are not able to estimate the off-diagonal elements, since the anisotropic contributions to U given by Eq. (20), which vanish with  $r^n$   $(n \ge 3)$ , are not known.

## B. Spin-Orbit Coupling

The spin-orbit matrix elements (14) between wave functions  $\phi_i$  and  $\chi_j$  vanish. Therefore, the degeneracy of the sextet consisting of the two states  ${}^{2}\Gamma_{7}$  and  ${}^{4}\Gamma_{8}$ remains unlifted [see Eq. (19) for the case of Ge]. This result is not restricted to the effective-mass approximation and holds also if the wave functions  $\phi_i$  and  $\chi_i$ are given in terms of the exact eigenfunctions of  $H_0$ which can be written in the form  $\psi_i = \sum_{n,\mathbf{k}} A_n(\mathbf{k} - \mathbf{k}_i)$  $\times \psi_n(\mathbf{k}-\mathbf{k}_i,\mathbf{r})$ . However, spin-orbit matrix elements (14) between wave functions  $\phi_i$  and  $\phi_j$  can be different from zero, according to the selection-rule theorem. Whether this is actually the case, if the  $\psi_i$  are given by the effective-mass approximation Eq. (6) with  $\psi_0$  $=\exp(i\mathbf{k}\cdot\mathbf{r})u_{\mathbf{k}}(\mathbf{r})$ , can be seen from the matrices<sup>15</sup>

$$M_{ij,2} = -\frac{\hbar^2}{4m^2c^2} \left[ \int_{u.c.} \exp(i(\mathbf{k}_j - \mathbf{k}_i) \cdot \mathbf{r}) \times u_{\mathbf{k}_i}^* (\nabla V \times i \nabla u_{\mathbf{k}_j})_x \frac{d\tau}{\Omega} + \int_{a.s.} \exp(i(\mathbf{k}_j - \mathbf{k}_i) \cdot \mathbf{r}) \times F_i^* F_j u_{\mathbf{k}_i}^* (\nabla U \times i \nabla u_{\mathbf{k}_j})_x d\tau \right].$$
(23)

It is assumed that the envelope functions  $F_i$  and their first derivatives are smooth functions of r. The first integral (over a unit cell) accounts for the effect of spin-orbit coupling on a Bloch state  $\mathbf{k}_i$ ; it is zero for all i, j as can be shown with the help of the selectionrule theorem.<sup>16</sup> Furthermore, the corresponding diagonal matrix element for an arbitrary state of the lowest ("s-like") conduction band vanishes, as can be seen by writing  $u_k(\mathbf{r})$  and  $V(\mathbf{r})$  as a Fourier series and then applying the relation  $u_k^* = au_{-k}$  ( $aa^* = 1$ ) which follows from the inversion symmetry of  $V(\mathbf{r})$ .<sup>17</sup> The second integral of Eq. (23) describes the effect of spin-orbit coupling on the effective-mass ground state; it can be shown that this integral also vanishes for all i, j.<sup>18</sup>

<sup>&</sup>lt;sup>15</sup> The integral can diverge in its present form. This divergence is a consequence of the approximation applied in reducing the four-component Dirac equation to the two-component Pauli equation. The difficulty is removed, as in the theory of atomic spectra, by replacing  $\nabla \mathbb{O}$  with  $(1-\mathbb{O}/2mc^2)^{-2}\nabla \mathbb{O}$ . <sup>16</sup> The Bloch state  $\mathbf{k}(\pi | a, \pi | a, \pi | a)$  (of the conduction band of Ge) transforms according to the small representation  $L_1$ ; the x,

y, and z components of a pseudo-vector transform according to  $L_3$  and  $L_2$ , respectively. The direct product  $(L_3+L_1) \times L_1$  does not contain  $L_1$ . However, in the second-order approximation of perturbation theory, the energy levels are determined by matrix elements between an  $L_1$  state and corresponding states of higher

elements between an  $L_1$  state and corresponding states of ingret conduction bands which may not vanish. <sup>17</sup> R. J. Elliott, Phys. Rev. **96**, 266 (1954). <sup>18</sup> Since the first integral of Eq. (23) vanishes, we have  $M_{i,j2} = \int \psi_i * h_x(U) \psi_j d\tau$ , where  $h_x(U) = -(\hbar^2/4m^2c^2) (\nabla U \times i \nabla)_x$ . This expression for  $M_{ij,2}$  leads to the second integral of Eq. (23), with our assumptions on  $F_i$  and on its first derivatives. For the case of germanium it is readily seen that  $M_{ij,2}$  vanishes. Using Elliott's relation and denoting with  $\psi_{-i}$  the effective-mass wave function for  $-\mathbf{k}_i$  which contains  $F_{-i}(\mathbf{r}) = F_i(\mathbf{r})$ , we find  $M_{ij,2} = -M_{-j-i,2}$ . The wave vectors  $\mathbf{k}_i$  and  $-\mathbf{k}_i$  differ by  $2\pi$  times a vector of the reciprocal lattice, thus  $M_{-j-i,2} = M_{ji,2}$ . Furthermore, since the

Hence, for Ge, there is no effect of spin-orbit coupling in first-order perturbation theory if the zero-order wave functions are taken from the effective-mass approximation Eq. (6). The same result holds for the effectivemass ground state of donors in Si. An upper limit for the second-order change of the energy of the effectivemass ground state is estimated roughly in Appendix B; it is found to be  $5 \times 10^{-5}$  eV for donor electrons in Ge.

The first-order effect on the exact eigenstates of  $H_0$  cannot be calculated, since it is not known to what extent Bloch functions of higher bands are admixed into the impurity wave functions because of the strong impurity potential in the central cell. An order of magnitude estimate for the ratio of the coefficients  $A_n(n\neq 0)$  and  $A_0$ , defined by Eq. (4), is given by Kohn.<sup>1</sup> From this estimate it is seen that the admixture for donors in Ge is much larger than for donors in Si. The different extent of admixture appears to be a characteristic distinction between impurity wave functions in Ge and Si. This distinction can be important for the g factors of donor electrons.<sup>19</sup>

## C. s-Shift and Mass-Velocity Correction

These corrections<sup>20</sup> do not contain the electron spin and, therefore, they cannot cause a splitting of the

 $M_{ij,2}$  are elements of a secular matrix and since these elements are real according to Eq. (19), we have  $M_{ij,2} = M_{ji,2}$  and, therefore, the matrix elements vanish.

 $^{20}$  F. Herman (private communication) has solved the Hartree-Fock-Slater wave equations for neutral germanium and silicon atoms and then applied first-order perturbation theory to account for the relativistic corrections. It is a pleasure to thank Dr. Herman for a number of interesting comments concerning the relativistic corrections on Bloch states and for making available to us his numerical results for the three relativistic corrections on atomic orbitals of germanium and silicon atoms. degenerate state  ${}^{2}\Gamma_{7}$  and  ${}^{4}\Gamma_{8}$ . However, since both the *s*-shift correction  $H_{3}$  and the mass-velocity correction  $H_{4}$  have the full tetrahedral symmetry, they can partly lift the 2*m*-fold degeneracy of the effective-mass ground state, as does the potential correction  $H_{1}$ . Let us compare the shift and the splitting caused by  $H_{3}$  and  $H_{4}$  with the corresponding effect of  $H_{1}$ . If one substitutes the effective-mass wave function into Eq. (15), the matrix elements of the *s*-shift correction are given by

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$$M_{ij,3} = -\frac{\hbar^2}{4m^2c^2} \left[ \frac{1}{\Omega} \int_{\mathbf{u}.\mathbf{c}.} \psi_0^*(\mathbf{k}_i \mathbf{r}) \nabla V \cdot \nabla \psi_0(\mathbf{k}_j, \mathbf{r}) d\tau + |F(0)|^2 \int_{\mathbf{c}.\mathbf{c}.} \psi_0^*(\mathbf{k}_i, \mathbf{r}) \nabla U \cdot \nabla \psi_0(\mathbf{k}_j, \mathbf{r}) d\tau \right]. \quad (24)$$

Similarly, the matrix elements of the mass-velocity correction are found as

$$M_{ij,4} = -\frac{1}{2mc^2} \left[ \frac{1}{\Omega} \int_{\mathbf{u}.\mathbf{v}.} \psi_0^*(\mathbf{k}_i,\mathbf{r}) (E_0+V)^2 \psi_0(\mathbf{k}_j,\mathbf{r}) d\tau + |F(0)|^2 \int_{\mathbf{v}.\mathbf{v}.} \psi_0^*(\mathbf{k}_i,\mathbf{r}) U(\mathbf{v}+V+2E_0) \psi_0(\mathbf{k}_i,\mathbf{r}) d\tau \right].$$
(25)

The second contribution to each matrix element has been restricted to the central cell where the potential U has a singularity. The first term of each of the two diagonal elements [Eqs. (24) and (25)] corresponds to the shift of the Bloch state of the conduction band minimum. For these terms there are no quantitative values available at present. However, Herman<sup>20</sup> has calculated the effect of all three relativistic corrections on the 3s and 3p atomic orbital of a free Si atom and on the 4s and 4p atomic orbital of a free Ge atom. His result for the s-shift correction to the 3s and 4s atomic states of Si and Ge is +0.16 and +0.93 eV, respectively, and the corresponding numbers for the mass-velocity correction are -0.62 and -1.62 eV. Hence, there is a partial cancellation of the two corrections. Assuming that the net shift of the conduction band minimum of Ge is  $\frac{1}{2}$  eV, we estimate roughly that the second terms of both diagonal elements, which describe the relative shift of the ground state with respect to the conduction band minimum, give a net shift of the order of magnitude  $\frac{1}{2}|F(0)|^{2}\Omega$  eV, for As and Sb donors. Thus, with the corrected envelope function, the shift amounts to  $\sim 5 \times 10^{-4}$  and  $\sim 5 \times 10^{-3}$  eV for As and Sb donor states in germanium and silicon, respectively.

The nondiagonal elements of Eqs. (24) and (25) contribute to the observed splitting of the degenerate effective-mass ground state (see Fig. 1). In the case of donor electrons in Ge, the relative contribution of the two relativistic corrections to the splitting between the  ${}^{2}\Gamma_{6}$  state and the  ${}^{2}\Gamma_{7}+{}^{4}\Gamma_{8}$  state is determined by the

<sup>&</sup>lt;sup>19</sup> A difference between the g factor of donor electrons and that approximative g factor for donor electrons given by L. M. Roth and B. Lax [Phys. Rev. Letters 3, 217 (1959), Eq. (5)] in terms of the tensor components gil and gi calculated for a single ellipsoidal energy surface of conduction electrons, may be caused to some extent by the admixture of Bloch functions from higher bands into the impurity wave function. For antimony, phosphorus, and arsenic impurities in Si, the g factors of donor electrons have been measured by D. K. Wilson and F. Feher [Phys. Rev. 124, 1068 (1961)]. For conduction electrons in Si, experimental values for the anisotropic g factor do not seem to be available. However, L. M. Roth [Phys. Rev. 118, 1534 (1960)], H. Hagesawa [Phys. Rev. 118, 1523 (1960)], and L. Liu [Phys. Rev. Letters 6, 683 (1961)] have calculated the g factor of conduction electrons in Si. The experimental result for the isotropic g factor of donor electrons and the theoretical result for the isotropic g factor of donor electrons and the theoretical result for the sotropic g factor of an and g are in the sotropic of a solution of the soluti and the theoretical result given in terms of  $g_{II}$  and  $g_{I}$  are in quantitative agreement. Thus, it appears that the impurity wave functions in Si are well described with the effective-mass approximation which neglects the admixture of Bloch functions from higher conduction bands. On the other hand, the experimental values of the g factors for donor electrons of phosphorus or arsenic impurities in Ge measured by G. Feher, D. K. Wilson, and E. A. Gere [Phys. Rev. Letters 3, 25 (1959)] are not in quantitative agreement with the theoretical value derived from  $g_{11}$  and  $g_1$  for an ellipsoidal energy surface of conduction electrons. The difference may be caused, as in the more subtle case of antimony-doped Ge (see Feher et al., Roth and Lax), to some extent by the admixture of Bloch functions from higher conduction bands into the impurity wave functions. An excellent review article on g factors (and spin-lattice relaxation) has been presented by Y. Yafet, in Solid-State Physics, edited by F. Seitz and D. Turnbull (Academic Press Inc., New York, 1963), Vol. 14, p. 1.

ratio

$$\frac{-\frac{1}{2mc^2}\int_{\mathbf{c.c.}}\psi_0^*(\mathbf{k}_i)U(\mathbf{U}+V+2E_0)\psi_0(\mathbf{k}_j)d\tau - \frac{\hbar^2}{4m^2c^2}\int_{\mathbf{c.c.}}\psi_0^*(\mathbf{k}_i)\nabla U\cdot\nabla\psi_0(\mathbf{k}_j)d\tau}{\int_{\mathbf{c.c.}}\psi_0^*(\mathbf{k}_i)(U-U_0)\psi_0(\mathbf{k}_j)d\tau}.$$
(26)

Since it is the anisotropic part of the potential  $U(\mathbf{r})$  which determines the integrals and since this part has no singularity at  $\mathbf{r}=0$ , the contribution of the relativistic corrections to the observed splitting is small compared to the valley-orbit contribution, even in the case of Sb donors in germanium where the splitting is an order of magnitude smaller than for P and As donors.

## **V. CONCLUSION**

The main purpose of this paper has been to discuss the possible importance of spin-orbit coupling and other relativistic corrections on the degenerate effectivemass ground state of shallow impurities in Ge and Si.

With the help of perturbation theory and the relevant selection-rule theorem, one finds that in first order, spin-orbit coupling does not affect the impurity ground states and, in particular, one finds that there is no splitting of the sextet state in Ge or Si. In second order, the effect of spin-orbit coupling is estimated to be of the order  $5 \times 10^{-5}$  eV or smaller. It is emphasized that these results depend on an assumption of the effectivemass theory; namely, the admixture of Bloch functions from higher conduction bands into the impurity wave function can be neglected.<sup>21</sup> If one could go beyond this approximation, one should expect a first-order effect of spin-orbit coupling on the impurity ground states in Ge or Si, since the Bloch states of higher "non-s-like" conduction bands are also affected by spin-orbit coupling in first order.

At present it is not known to what quantitative extent Bloch functions from higher bands are admixed into the impurity wave function.<sup>22</sup> Kohn's order of magnitude estimate indicates, however, that the admixture is considerably larger for impurity states in Ge than it is for those in Si. The admixture will determine, to some extent, the difference between the g factor of a donor electron and the appropriate g factor of the conduction electrons. For Si there is no such difference (see Ref. 19). For Ge there is a small difference (to our knowledge there are no available experimental g values for the conduction electrons). As for the two other relativistic corrections, namely the s-shift correction and the mass-velocity correction, they do not depend on the spin and they have the symmetry of  $U(\mathbf{r})$ . Their effect on the degenerate effective-mass ground state consists of a binding energy increase of the order of 10%. The splitting caused by these corrections is determined by the anisotropic part of U which—due to the tetrahedral symmetry of U vanishes with  $r^n(n\geq 3)$  for  $r \rightarrow 0$ . Therefore, the splitting is small compared with the valley-orbit splitting.

Thus, it can be seen that, although spin-orbit coupling and the other relativistic corrections are of some importance for the binding energy of the impurity states, and for the g factors of donor electrons, the relativistic corrections cannot account for the observed energy level structure of the impurity ground states. Spin-orbit coupling will not result in an additional splitting of degenerate energy levels large enough to be observed with present experimental techniques. As for the relative importance of corrections (1), (2), and (3), it appears that the potential correction  $U-U_0$ , i.e., correction (1), which lowers the effective-mass binding energy and causes the valley-orbit splitting, is the most important one, at least for donor states in Si. Thus, an accurate computation of the U's for different impurities in Si would be of considerable interest. For Ge the admixture of Bloch functions from higher bands may also be of some importance (see Ref. 19 for g factors of donor electrons). In such a case the small observed valley-orbit splitting of antimony donors, which is by an order of magnitude smaller than for phosphorus and arsenic donors, can be caused by a partial compensation of the non-relativistic corrections (1) and (2).

## ACKNOWLEDGMENTS

It is a pleasure to thank W. Kohn for a number of stimulating discussions on the subject of this paper. For a critical reading of the manuscript and for some constructive comments, I am indebted to W. Kleiner, Lincoln Laboratory.

# APPENDIX A: THE COEFFICIENTS $\alpha_i^{rs}$ AND $\beta_i^{rs}$ (Ge)

The correct zero-order wave functions given by Eq. (8) can be determined by symmetry considerations. To this end, let us write the wave functions of the Kohn-Luttinger Hamiltonian  $H_0$  which are obtained in the effective-mass approximation and which trans-

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<sup>&</sup>lt;sup>21</sup> Since the Bloch states of a higher "non-s-like" conduction band will be affected to a different degree, depending on the particular  $\mathbf{k}$ , by spin-orbit coupling (or by the other relativistic corrections), the effect of the admixture will certainly depend on the composition of the impurity wave function in terms of higher band Bloch states.

band Bloch states. <sup>22</sup> The admixture of a higher band Bloch state  $\mathbf{k}$  into the impurity wave function will depend on the strength of the impurity potential in the central cell and on the energy gap between the energy of the state  $\mathbf{k}$  and the conduction band minimum.

form according to the representations  $T_1$  and  $T_3$  of the tetrahedral point group  $T_d$ , in the form

$$\Psi^{(1)} = \sum_{i} a_{i}^{(1)} \psi_{i}, \quad \Psi_{j}^{(3)} = \sum_{i} a_{ij}^{(3)} \psi_{i}, \quad (j = 1, 2, 3), \quad (A1)$$

where  $\psi_i$  is given by Eq. (6). If we number the minima of the conduction band in the (1, -1, -1), (-1, 1, -1), (1,1,1), (-1, -1, 1) directions by 1, 2, 3, 4, the coefficients  $a_2^{(i)}$  and  $a_{3i}^{(i)}$  (i=1, 2, 3, 4) are given by:

for  $(T_1)$ 

 $a_i^{(1)} = \frac{1}{2}(1,1,1,1),$ and for  $(T_3)$ ,

$$a_{i1},^{(3)} = \frac{1}{2}(1, -1, -1, 1), \qquad (A2)$$
  

$$a_{i2},^{(3)} = \frac{1}{2}(1, -1, 1, -1), \qquad (A2)$$
  

$$a_{i3},^{(3)} = \frac{1}{2}(1, 1, -1, -1).$$

With the help of Eqs. (A1) and (A2) the two-component wave functions transforming according to the representations  ${}^{2}\Gamma_{6}$ ,  ${}^{2}\Gamma_{7}$ , and  ${}^{4}\Gamma_{8}$  can be determined immediately. The first case ( ${}^{2}\Gamma_{6}$ ) is trivial. In order to determine the wave functions associated with  ${}^{2}\Gamma_{7}$  and  ${}^{4}\Gamma_{8}$ , let us write

$$X = \sum_{i} a_{i1}{}^{(3)}\phi_{i}, \quad Y = \sum a_{i2}{}^{(3)}\phi_{i}, \quad Z = \sum a_{i3}{}^{(3)}\phi_{i}, \quad (A3)$$

where  $\phi_i$  is given by Eq. (9). In terms of these functions and their time reversal conjugates (indicated by a bar), the correct zero-order wave functions are given by: for  $({}^2\Gamma_7)$ 

$$\Psi_{17} = (1/\sqrt{3})(\bar{X} - i\bar{Y} + Z), \quad \Psi_{27} = K\Psi_{17}$$

and for  $({}^{2}\Gamma_{8})$ 

$$\Psi_{18} = (1/\sqrt{2})(X+iY), \qquad \Psi_{38} = K\Psi_{28}, \quad (A4)$$
  
$$\Psi_{28} = (1/6^{1/2})(\bar{X}+i\bar{Y}-2Z), \quad \Psi_{48} = K\Psi_{18}.$$

#### APPENDIX B: SPIN-ORBIT COUPLING IN SECOND ORDER (Ge)

An upper limit for the second order change of the energy of the effective-mass ground state is given by

$$E_2 = \int_{a.s.} (\psi_i u_\alpha)^* H_{so}^2 \psi_i u_\alpha d\tau / \Delta E, \qquad (B1)$$

where  $\Delta E \sim 1$  eV. Let us assume that in the vicinity of an impurity nucleus the effective-mass wave function can be written in the form

$$\psi_i(\text{Ge}) = F(\mathbf{r}) \left(\Omega/2\right)^{1/2} \left[ a(\mathbf{k}_i) \psi_{4s} + b(\mathbf{k}_i) \psi_{4p} \right], \quad (B2)$$

where  $\psi_{4s}$  and  $\psi_{4p}$  are normalized atomic orbitals of a free Ge atom. The dominant contribution to the matrix element of Eq. (B1) comes from inside the central cell. In the limit where  $r \rightarrow 0$ , the potential has the form

$$U(\mathbf{r}) = -[e^2(Z_d - Z_0)/r] + \text{const}xyz. \quad (B3)$$

Clearly, it is the Coulombic term of the potential which, together with the 4p orbital in  $\psi_i$ , determines the value of  $E_2$ ; one finds

$$E_2 = (|F(0)|^2 \Omega b^2/2) [(Z_d - Z_0)/Z_0]^2 \mathcal{E}_2(4p), \quad (B4)$$

where  $\mathcal{E}_2(4p)$  is an upper limit for the second order change of the atomic 4p orbital given by

$$\mathcal{S}_{2}(4p) = \left(\frac{\hbar^{2}}{4m^{2}c^{2}}\right)^{2} \frac{1}{\Delta E a_{0}^{4}} \left(\frac{Z_{0}e^{2}}{a_{0}}\right)^{2} \times \frac{4\pi}{3} \int_{a.s.} \frac{(R_{4p})^{2}dr}{r^{4}(1+Z_{d}r_{0}/2r)^{4}}, \quad (B5)$$

where  $a_0$  is the Bohr radius. This quantity can be calculated without difficulty if one substitutes for the radial eigenfunction  $R_{4p}$ , the approximative formula which applies for  $r/a_0 \ll n^2/Z^{23}$  The resulting upper limit  $\mathcal{E}_2(4p)$  gives an unrealistic large value for the actual second-order change of the atomic 4p orbital. Therefore,  $E_2$  is estimated roughly by substituting for  $\mathcal{E}_2(4p)$  the value found by Herman<sup>20</sup> for the first-order correction of the 4p orbital, 0.071 eV. Taking  $b^2 = 1/10$ and assuming that the corrected value for  $|F(0)|^2$  is larger by a factor of ten than the corresponding value for the effective-mass envelope function, one finds  $E_2 < 5 \times 10^{-5}$  eV.

<sup>23</sup> H. A. Bethe and E. E. Salpeter, in *Encyclopedia of Physics*, edited by S. Flügge (Springer-Verlag, Berlin, 1957), Vol. 35, p. 1.